Foreword

Research into wide band gap semiconductor materials has continued to expand each year, with an ever increasing array of devices being developed for applications as diverse as power electronics, optical emitters, and solar cells. The *Journal of Electronic Materials* has published a special issue on these research efforts for 17 consecutive years. While this special issue was originally designed to focus on SiC and III-nitride semiconductors, the developments made in ZnO and II–VI oxide semiconductor materials in the early part of the past decade caused the expansion of the issue in 2004 to include these materials as well.

Research in epitaxial growth, materials characterization, device processing, and development are all included in the special issue, with many of the papers initially having been presented at the 52nd Electronic Materials Conference (EMC) that was held in June of 2010 at Notre Dame University. The conference remains a lively annual forum for the discussion of research in the area of wide band gap semiconductors.

This special issue is the result of the significant effort invested by the various authors, reviewers, editors, and journal staff members. They all deserve our deepest thanks for their invaluable contributions.

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